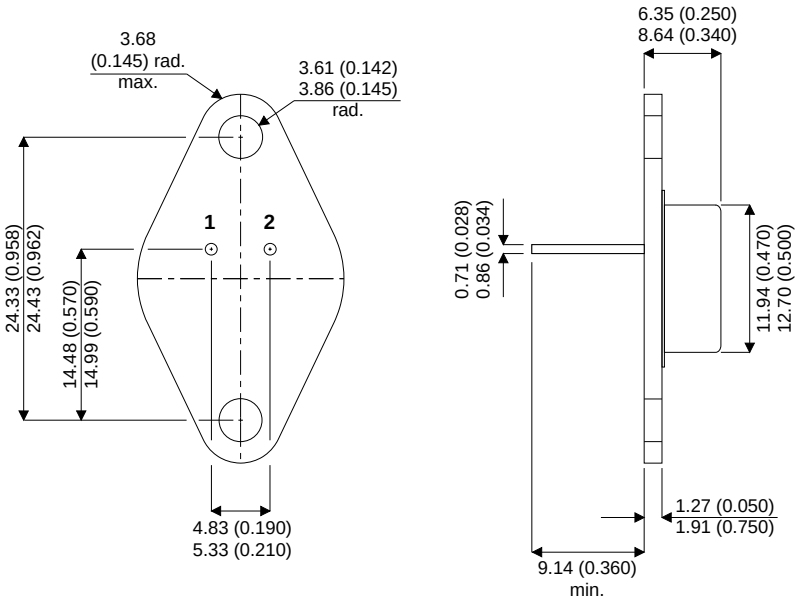
2N4910X
2N4911X
2N4912X

MECHANICAL DATA
Dimensions in mm (inches)



TO–66 Metal Package.

PIN 1 = BASE PIN 2 = EMITTER CASE = COLLECTOR

NPN EPITAXIAL POWER TRANSISTOR IN TO66 HERMETIC PACKAGE

APPLICATIONS
- **SCREENING OPTIONS AVAILABE**
- **TO66 PACKAGE**

ABSOLUTE MAXIMUM RATINGS

	(T_{case} = 25°C unless otherwise stated)	2N4910X	2N4911X	2N4912X
$V_{(BR)CBO}$	Collector – Base Breakdown Voltage	40V	60V	80V
$V_{(BR)CEO}$	Collector – Emitter Breakdown Voltage	40V	60V	80V
$V_{(BR)EBO}$	Emitter – Base Breakdown Voltage		5V	
I_C	Continuous Collector Current		4A	
I_B	Base Current		1A	
P_D	Total Power Dissipation		25W	
T_C	Operating Case Temperature Range		–65 to +200°C	
T_{stg}	Storage Temperature Range		–65 to +200°C	
$R_{\theta JC}$	Thermal Resistance , Junction To Case		7.0°C/W	

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E-mail: sales@semelab.co.uk Website: http://www.semelab.co.uk

Electrical Characteristics (T_C = 25°C unless otherwise stated.)

	Parameter	Test Conditions		Min.	Typ.	Max.	Units
I_{CEO}	Collector – Emitter Cut-off Current	V_{CE} = 30V	I_B = 0			0.50	mA
I_{CEX}	Collector – Emitter Cut-off Current	$V_{CE} = V_{(BR)CEO}$	V_{BE} = 1.5V			100	µA
			T_C = 150°C			1.0	mA
I_{CBO}	Collector – Base Cut-off Current	$V_{CB} = V_{(BR)CBO}$	I_E = 0			0.1	mA
I_{CES}	Collector – Emitter Leakage Current	$V_{CE} = V_{(BR)CEO}$	V_{BE} = 0			100	µA
$V_{CE(sat)}$*	Collector – Emitter Saturation Voltage	I_C = 1A	I_B = 0.1A			0.60	V
$V_{BE(sat)}$*	Base – Emitter Saturation Voltage	I_C = 1A	I_B = 0.1A			1.3V	V
V_{BE}*	Base – Emitter Voltage	I_C = 1A	V_{CE} = 1V			1.3V	V
h_{FE}*	DC Current Gain	V_{CE} = 1V	I_C = .5mA	20		175	—
		V_{CE} = 1V	I_C = 1mA	10			
		V_{CE} = 1V	I_C = .05A	40			

* Pulse Test: t_p = 300µs, δ = 2%.